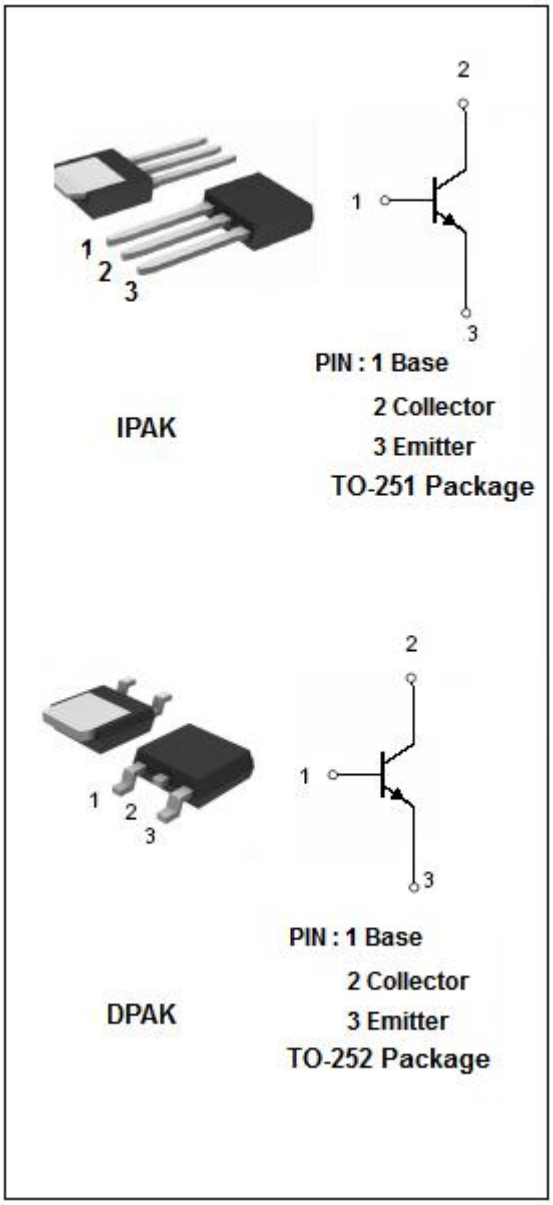
isc Silicon NPN Power Transistor KSH50

DESCRIPTION

- Lead formed for surface mount applications(NO suffix)
- Straight lead(IPAK, "－I" suffix)
- Electrically similar to popular TIP50
- High voltage and high reliability
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- designed for line operated audio output amplifier



ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	500	V
V_{CEO}	Collector-Emitter Voltage	400	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	1	A
I_{CP}	Collector Current-Pulse	2	A
P_C	Total Power Dissipation @ Ta=25℃	1.56	W
P_C	Total Power Dissipation @ T_C=25℃	15	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$V_{(BR)CEO}$*	Collector-Emitter Breakdown Voltage	I_C= 30mA; I_B= 0	400			V
$V_{CE(sat)}$*	Collector-Emitter Saturation Voltage	I_C=1A; I_B= 200mA			1.0	V
$V_{BE(on)}$*	Base-Emitter On Voltage	I_C= 1A; V_{CE}=10V			1.5	V
I_{CEO}	Collector Cutoff Current	V_{CE}= 300V; I_E= 0			0.2	mA
I_{EBO}	Emitter Cutoff Current	V_{EB}= 5V; I_C= 0			1	mA
h_{FE1}*	DC Current Gain	I_C= 0.3A; V_{CE}= 10 V	30		150	
h_{FE2}*	DC Current Gain	I_C= 1A; V_{CE}= 10 V	10			
f_T	Current-Gain—Bandwidth Product	I_C= 0.2A; V_{CE}= 10V	10			MHz

*:Pulse test PW≤300us,duty cycle≤2%

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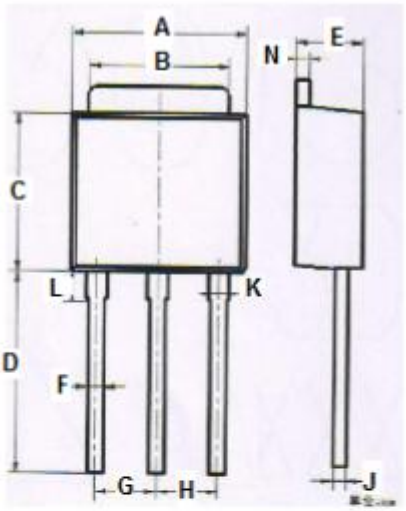
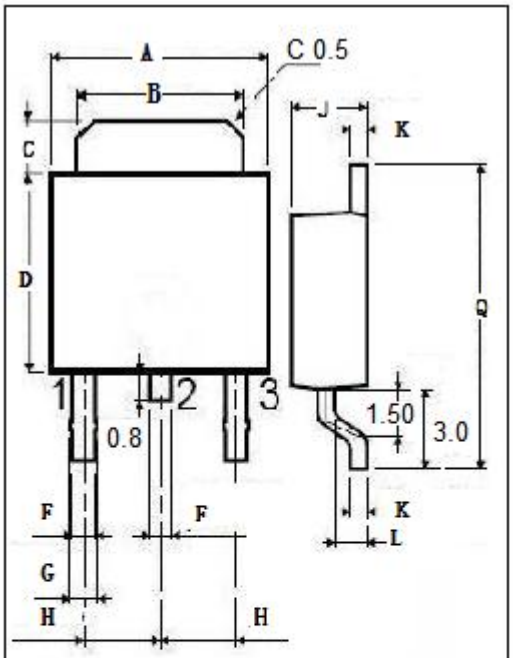
Outline Drawing



DIM	mm MIN	MAX
A	6.40	6.48
B	5.10	5.50
C	5.80	6.20
D	9.20	9.60
E	2.20	2.40
F	0.50	0.70
G	2.09	2.49
H	2.09	2.49
J	0.40	0.60
K	0.70	0.90
L	1.60	2.00
N	0.40	0.60



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1